

# 2SC2620

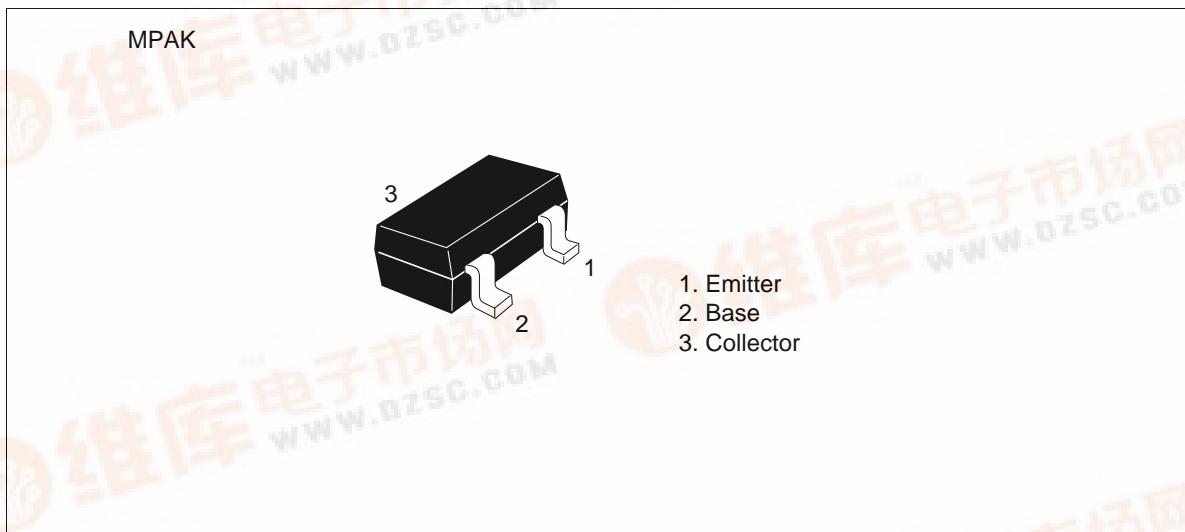
Silicon NPN Epitaxial Planar

**HITACHI**

## Application

VHF amplifier, Local oscillator

## Outline



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## 2SC2620

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	V <sub>EBO</sub>	4	V
Collector current	I <sub>C</sub>	20	mA
Collector power dissipation	P <sub>C</sub>	100	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>STG</sub>	-55 to +150	°C

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### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	30	—	—	V	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	20	—	—	V	I <sub>C</sub> = 1 mA, R <sub>BE</sub> = ∞
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	4	—	—	V	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0
Collector cutoff current	I <sub>CBO</sub>	—	—	0.5	μA	V <sub>CB</sub> = 10 V, I <sub>C</sub> = 0
Emitter cutoff current	I <sub>EBO</sub>	—	—	0.5	μA	V <sub>EB</sub> = 2 V, I <sub>C</sub> = 0
DC current transfer ratio	h <sub>FE</sub> <sup>*1</sup>	60	—	200		V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	—	0.17	—	V	I <sub>C</sub> = 20 mA, I <sub>B</sub> = 4 mA
Base to emitter voltage	V <sub>BE</sub>	—	0.72	—	V	V <sub>CE</sub> = 6 mA, I <sub>C</sub> = 1 mA
Gain bandwidth product	f <sub>T</sub>	—	940	—	MHz	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 5 mA
Collector output capacitance	C <sub>OB</sub>	—	0.9	—	pF	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz

Note: 1. The 2SC2620 is grouped by h<sub>FE</sub> as follows.

Grade	B	C
Mark	QB	QC
h <sub>FE</sub>	60 to 120	100 to 200

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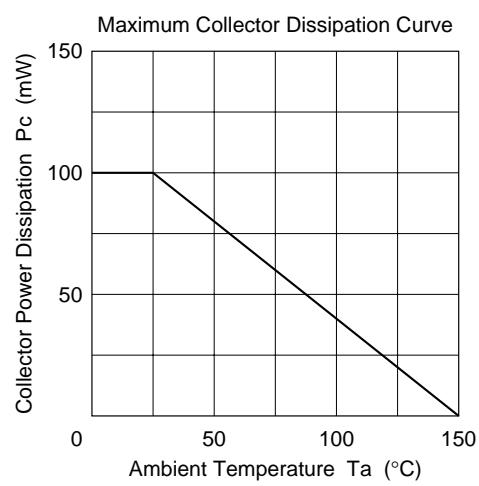
See characteristic curves of 2SC535.

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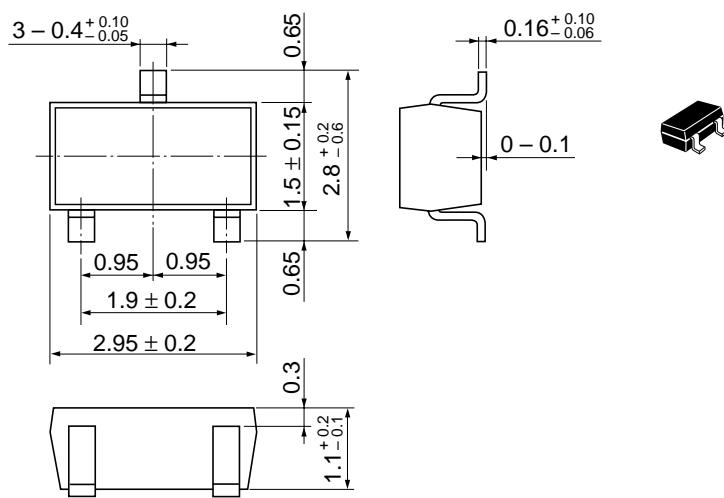
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**2SC2620**

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Unit: mm



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